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Understanding Embedded - FPGAs (Field Programmable Gate Array)

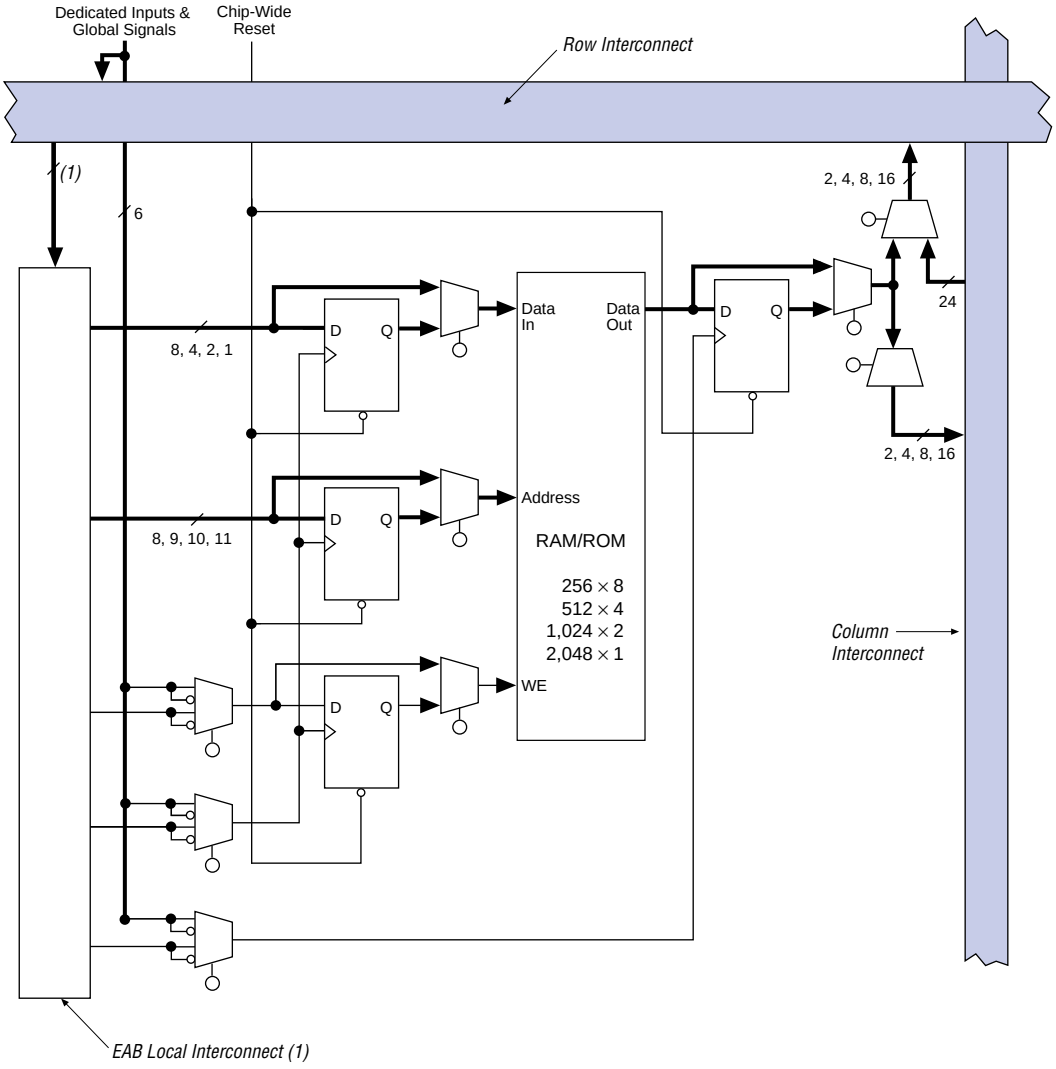
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	20480
Number of I/O	189
Number of Gates	116000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP Exposed Pad
Supplier Device Package	240-RQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50rc240-4

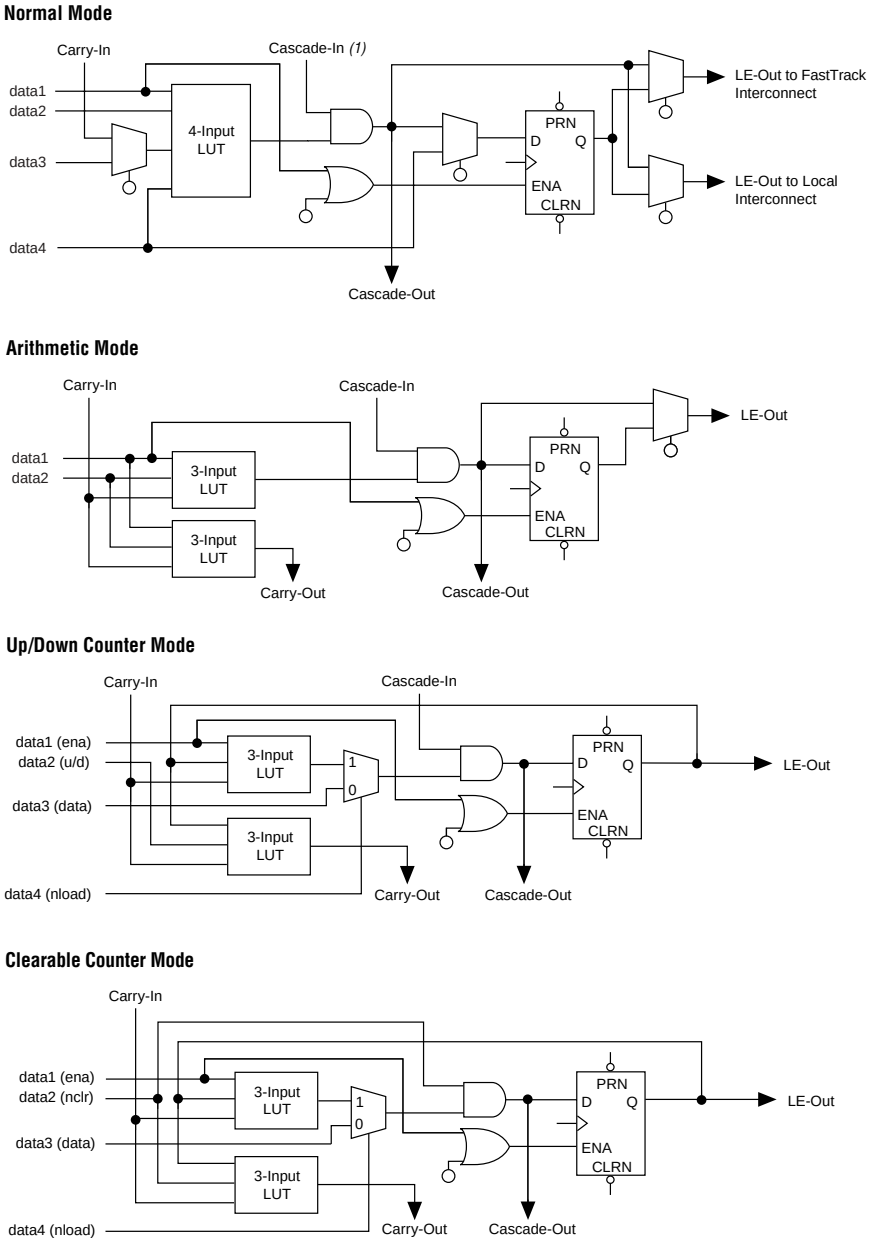
Figure 4. FLEX 10K Embedded Array Block



Note:

(1) EPF10K10, EPF10K10A, EPF10K20, EPF10K30, EPF10K30A, EPF10K40, EPF10K50, and EPF10K50V devices have 22 EAB local interconnect channels; EPF10K70, EPF10K100, EPF10K100A, EPF10K130V, and EPF10K250A devices have 26.

Figure 9. FLEX 10K LE Operating Modes



Note:
(1) Packed registers cannot be used with the cascade chain.

Asynchronous Preset

An asynchronous preset is implemented as either an asynchronous load, or with an asynchronous clear. If DATA3 is tied to V_{CC}, asserting LABCTRL1 asynchronously loads a one into the register. Alternatively, the Altera software can provide preset control by using the clear and inverting the input and output of the register. Inversion control is available for the inputs to both LEs and IOEs. Therefore, if a register is preset by only one of the two LABCTRL signals, the DATA3 input is not needed and can be used for one of the LE operating modes.

Asynchronous Preset & Clear

When implementing asynchronous clear and preset, LABCTRL1 controls the preset and LABCTRL2 controls the clear. DATA3 is tied to V_{CC}, therefore, asserting LABCTRL1 asynchronously loads a one into the register, effectively presetting the register. Asserting LABCTRL2 clears the register.

Asynchronous Load with Clear

When implementing an asynchronous load in conjunction with the clear, LABCTRL1 implements the asynchronous load of DATA3 by controlling the register preset and clear. LABCTRL2 implements the clear by controlling the register clear; LABCTRL2 does not have to feed the preset circuits.

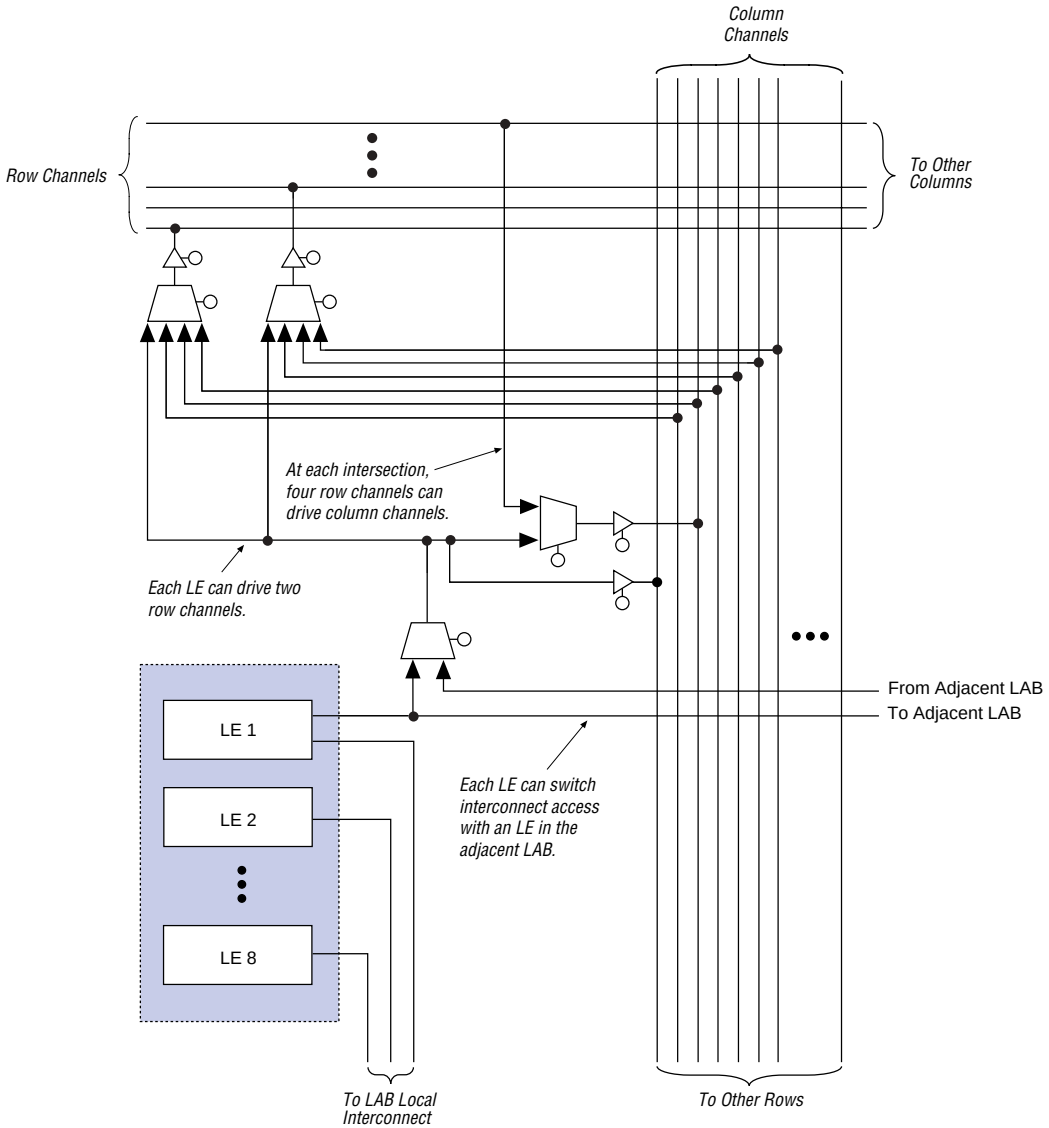
Asynchronous Load with Preset

When implementing an asynchronous load in conjunction with preset, the Altera software provides preset control by using the clear and inverting the input and output of the register. Asserting LABCTRL2 presets the register, while asserting LABCTRL1 loads the register. The Altera software inverts the signal that drives DATA3 to account for the inversion of the register's output.

Asynchronous Load without Preset or Clear

When implementing an asynchronous load without preset or clear, LABCTRL1 implements the asynchronous load of DATA3 by controlling the register preset and clear.

Figure 11. LAB Connections to Row & Column Interconnect



For improved routing, the row interconnect is comprised of a combination of full-length and half-length channels. The full-length channels connect to all LABs in a row; the half-length channels connect to the LABs in half of the row. The EAB can be driven by the half-length channels in the left half of the row and by the full-length channels. The EAB drives out to the full-length channels. In addition to providing a predictable, row-wide interconnect, this architecture provides increased routing resources. Two neighboring LABs can be connected using a half-row channel, thereby saving the other half of the channel for the other half of the row.

Table 7 summarizes the FastTrack Interconnect resources available in each FLEX 10K device.

Table 7. FLEX 10K FastTrack Interconnect Resources

Device	Rows	Channels per Row	Columns	Channels per Column
EPF10K10 EPF10K10A	3	144	24	24
EPF10K20	6	144	24	24
EPF10K30 EPF10K30A	6	216	36	24
EPF10K40	8	216	36	24
EPF10K50 EPF10K50V	10	216	36	24
EPF10K70	9	312	52	24
EPF10K100 EPF10K100A	12	312	52	24
EPF10K130V	16	312	52	32
EPF10K250A	20	456	76	40

In addition to general-purpose I/O pins, FLEX 10K devices have six dedicated input pins that provide low-skew signal distribution across the device. These six inputs can be used for global clock, clear, preset, and peripheral output enable and clock enable control signals. These signals are available as control signals for all LABs and IOEs in the device.

The dedicated inputs can also be used as general-purpose data inputs because they can feed the local interconnect of each LAB in the device. However, the use of dedicated inputs as data inputs can introduce additional delay into the control signal network.

ClockLock & ClockBoost Features

To support high-speed designs, selected FLEX 10K devices offer optional ClockLock and ClockBoost circuitry containing a phase-locked loop (PLL) that is used to increase design speed and reduce resource usage. The ClockLock circuitry uses a synchronizing PLL that reduces the clock delay and skew within a device. This reduction minimizes clock-to-output and setup times while maintaining zero hold times. The ClockBoost circuitry, which provides a clock multiplier, allows the designer to enhance device area efficiency by sharing resources within the device. The ClockBoost feature allows the designer to distribute a low-speed clock and multiply that clock on-device. Combined, the ClockLock and ClockBoost features provide significant improvements in system performance and bandwidth.

The ClockLock and ClockBoost features in FLEX 10K devices are enabled through the Altera software. External devices are not required to use these features. The output of the ClockLock and ClockBoost circuits is not available at any of the device pins.

The ClockLock and ClockBoost circuitry locks onto the rising edge of the incoming clock. The circuit output can only drive the clock inputs of registers; the generated clock cannot be gated or inverted.

The dedicated clock pin (`GCLK1`) supplies the clock to the ClockLock and ClockBoost circuitry. When the dedicated clock pin is driving the ClockLock or ClockBoost circuitry, it cannot drive elsewhere in the device.

In designs that require both a multiplied and non-multiplied clock, the clock trace on the board can be connected to `GCLK1`. With the Altera software, `GCLK1` can feed both the ClockLock and ClockBoost circuitry in the FLEX 10K device. However, when both circuits are used, the other clock pin (`GCLK0`) cannot be used. Figure 17 shows a block diagram of how to enable both the ClockLock and ClockBoost circuits in the Altera software. The example shown is a schematic, but a similar approach applies for designs created in AHDL, VHDL, and Verilog HDL. When the ClockLock and ClockBoost circuits are used simultaneously, the input frequency parameter must be the same for both circuits. In Figure 17, the input frequency must meet the requirements specified when the ClockBoost multiplication factor is two.

Table 19. FLEX 10K 5.0-V Device DC Operating Conditions *Notes (5), (6)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		V_{CCINT} + 0.5	V
V_{IL}	Low-level input voltage		–0.5		0.8	V
V_{OH}	5.0-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 4.75 V *(7)*	2.4			V
	3.3-V high-level TTL output voltage	I_{OH} = –4 mA DC, V_{CCIO} = 3.00 V *(7)*	2.4			V
	3.3-V high-level CMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(7)*	V_{CCIO} – 0.2			V
V_{OL}	5.0-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 4.75 V *(8)*			0.45	V
	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(8)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(8)*			0.2	V
I_I	Input pin leakage current	V_I = V_{CC} or ground *(9)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = V_{CC} or ground *(9)*	–40		40	µA
I_{CC0}	V_{CC} supply current (standby)	V_I = ground, no load		0.5	10	mA

Table 20. 5.0-V Device Capacitance of EPF10K10, EPF10K20 & EPF10K30 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Table 21. 5.0-V Device Capacitance of EPF10K40, EPF10K50, EPF10K70 & EPF10K100 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		15	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		10	pF

Table 35. EAB Timing Macroparameters *Notes (1), (6)*		
Symbol	**Parameter**	**Conditions**
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Table 40. EPF10K10 & EPF10K20 Device IOE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{IOD}		1.3		1.6	ns
t_{IOC}		0.5		0.7	ns
t_{IOCO}		0.2		0.2	ns
t_{IOCOMB}		0.0		0.0	ns
t_{IOSU}	2.8		3.2		ns
t_{IOH}	1.0		1.2		ns
t_{IOCLR}		1.0		1.2	ns
t_{OD1}		2.6		3.5	ns
t_{OD2}		4.9		6.4	ns
t_{OD3}		6.3		8.2	ns
t_{XZ}		4.5		5.4	ns
t_{ZX1}		4.5		5.4	ns
t_{ZX2}		6.8		8.3	ns
t_{ZX3}		8.2		10.1	ns
t_{INREG}		6.0		7.5	ns
t_{IOFD}		3.1		3.5	ns
t_{INCOMB}		3.1		3.5	ns

Table 43. EPF10K10 Device Interconnect Timing Microparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
$t_{DIN2IOE}$		4.8		6.2	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		3.4		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.6		3.8	ns
$t_{SAMECOLUMN}$		0.9		1.1	ns
$t_{DIFFROW}$		4.5		4.9	ns
$t_{TWOROWS}$		8.1		8.7	ns
$t_{LEPERIPH}$		3.3		3.9	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Table 44. EPF10K20 Device Interconnect Timing Microparameters *Note (1)*					
Symbol	**-3 Speed Grade**		**-4 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	
$t_{DIN2IOE}$		5.2		6.6	ns
t_{DIN2LE}		2.6		3.8	ns
$t_{DIN2DATA}$		4.3		5.2	ns
$t_{DCLK2IOE}$		4.3		4.0	ns
$t_{DCLK2LE}$		2.6		3.8	ns
$t_{SAMELAB}$		0.6		0.6	ns
$t_{SAMEROW}$		3.7		3.9	ns
$t_{SAMECOLUMN}$		1.4		1.6	ns
$t_{DIFFROW}$		5.1		5.5	ns
$t_{TWOROWS}$		8.8		9.4	ns
$t_{LEPERIPH}$		4.7		5.6	ns
$t_{LABCARRY}$		0.5		0.8	ns
$t_{LABCASC}$		2.7		3.0	ns

Tables 48 through 56 show EPF10K30, EPF10K40, and EPF10K50 device internal and external timing parameters.

Table 48. EPF10K30, EPF10K40 & EPF10K50 Device LE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{LUT}		1.3		1.8	ns
t_{CLUT}		0.6		0.6	ns
t_{RLUT}		1.5		2.0	ns
t_{PACKED}		0.5		0.8	ns
t_{EN}		0.9		1.5	ns
t_{CICO}		0.2		0.4	ns
t_{CGEN}		0.9		1.4	ns
t_{CGENR}		0.9		1.4	ns
t_{CASC}		1.0		1.2	ns
t_{C}		1.3		1.6	ns
t_{CO}		0.9		1.2	ns
t_{COMB}		0.6		0.6	ns
t_{SU}	1.4		1.4		ns
t_{H}	0.9		1.3		ns
t_{PRE}		0.9		1.2	ns
t_{CLR}		0.9		1.2	ns
t_{CH}	4.0		4.0		ns
t_{CL}	4.0		4.0		ns

Table 75. EPF10K50V Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.7		6.0		7.1		8.2	ns
t_{DIN2LE}		2.5		2.6		3.1		3.9	ns
$t_{DIN2DATA}$		4.4		5.9		6.8		7.7	ns
$t_{DCLK2IOE}$		2.5		3.9		4.7		5.5	ns
$t_{DCLK2LE}$		2.5		2.6		3.1		3.9	ns
$t_{SAMELAB}$		0.2		0.2		0.3		0.3	ns
$t_{SAMEROW}$		2.8		3.0		3.2		3.4	ns
$t_{SAMECOLUMN}$		3.0		3.2		3.4		3.6	ns
$t_{DIFFROW}$		5.8		6.2		6.6		7.0	ns
$t_{TWOROWS}$		8.6		9.2		9.8		10.4	ns
$t_{LEPERIPH}$		4.5		5.5		6.1		7.0	ns
$t_{LABCARRY}$		0.3		0.4		0.5		0.7	ns
$t_{LABCASC}$		0.0		1.3		1.6		2.0	ns

Table 76. EPF10K50V Device External Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{DRR}		11.2		14.0		17.2		21.1	ns
t_{INSU} *(2), (3)*	5.5		4.2		5.2		6.9		ns
t_{INH} *(3)*	0.0		0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns

Table 77. EPF10K50V Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.0		2.8		3.5		4.1		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.9	2.0	7.8	2.0	9.5	2.0	11.1	ns
$t_{XZBIDIR}$		8.0		9.8		11.8		14.3	ns
$t_{ZXBIDIR}$		8.0		9.8		11.8		14.3	ns

Table 80. EPF10K130V Device EAB Internal Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.9		2.4		2.4	ns
$t_{EABDATA2}$		3.7		4.7		4.7	ns
t_{EABWE1}		1.9		2.4		2.4	ns
t_{EABWE2}		3.7		4.7		4.7	ns
t_{EABCLK}		0.7		0.9		0.9	ns
t_{EABCO}		0.5		0.6		0.6	ns
$t_{EABBYPASS}$		0.6		0.8		0.8	ns
t_{EABSU}	1.4		1.8		1.8		ns
t_{EABH}	0.0		0.0		0.0		ns
t_{AA}		5.6		7.1		7.1	ns
t_{WP}	3.7		4.7		4.7		ns
t_{WDSU}	4.6		5.9		5.9		ns
t_{WDH}	0.0		0.0		0.0		ns
t_{WASU}	3.9		5.0		5.0		ns
t_{WAH}	0.0		0.0		0.0		ns
t_{WO}		5.6		7.1		7.1	ns
t_{DD}		5.6		7.1		7.1	ns
t_{EABOUT}		2.4		3.1		3.1	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	4.0		4.7		4.7		ns

Table 86. EPF10K10A Device IOE Timing Microparameters *Note (1)* *(Part 2 of 2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOH}	0.8		1.0		1.3		ns
t_{IOCLR}		1.2		1.4		1.9	ns
t_{OD1}		1.2		1.4		1.9	ns
t_{OD2}		2.9		3.5		4.7	ns
t_{OD3}		6.6		7.8		10.5	ns
t_{XZ}		1.2		1.4		1.9	ns
t_{ZX1}		1.2		1.4		1.9	ns
t_{ZX2}		2.9		3.5		4.7	ns
t_{ZX3}		6.6		7.8		10.5	ns
t_{INREG}		5.2		6.3		8.4	ns
t_{IOFD}		3.1		3.8		5.0	ns
t_{INCOMB}		3.1		3.8		5.0	ns

Table 94. EPF10K30A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		5.5		6.5		8.5	ns
$t_{EABDATA2}$		1.1		1.3		1.8	ns
t_{EABWE1}		2.4		2.8		3.7	ns
t_{EABWE2}		2.1		2.5		3.2	ns
t_{EABCLK}		0.0		0.0		0.2	ns
t_{EABCO}		1.7		2.0		2.6	ns
$t_{EABBYPASS}$		0.0		0.0		0.3	ns
t_{EABSU}	1.2		1.4		1.9		ns
t_{EABH}	0.1		0.1		0.3		ns
t_{AA}		4.2		5.0		6.5	ns
t_{WP}	3.8		4.5		5.9		ns
t_{WDSU}	0.1		0.1		0.2		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	0.1		0.1		0.2		ns
t_{WAH}	0.1		0.1		0.2		ns
t_{WO}		3.7		4.4		6.4	ns
t_{DD}		3.7		4.4		6.4	ns
t_{EABOUT}		0.0		0.1		0.6	ns
t_{EABCH}	3.0		3.5		4.0		ns
t_{EABCL}	3.8		4.5		5.9		ns

Table 95. EPF10K30A Device EAB Internal Timing Macroparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{EABAA}		9.7		11.6		16.2	ns
$t_{EABRCCOMB}$	9.7		11.6		16.2		ns
$t_{EABRCREG}$	5.9		7.1		9.7		ns
t_{EABWP}	3.8		4.5		5.9		ns
$t_{EABWCCOMB}$	4.0		4.7		6.3		ns
$t_{EABWCREG}$	9.8		11.6		16.6		ns
t_{EABDD}		9.2		11.0		16.1	ns
$t_{EABDATACO}$		1.7		2.1		3.4	ns
$t_{EABDATASU}$	2.3		2.7		3.5		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	3.3		3.9		4.9		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	3.2		3.8		5.0		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.7		4.4		5.1		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		6.1		7.3		11.3	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 99 through 105 show EPF10K100A device internal and external timing parameters.

Table 99. EPF10K100A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.0		1.2		1.4	ns
t_{CLUT}		0.8		0.9		1.1	ns
t_{RLUT}		1.4		1.6		1.9	ns
t_{PACKED}		0.4		0.5		0.5	ns
t_{EN}		0.6		0.7		0.8	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.4		0.4		0.6	ns
t_{CGENR}		0.6		0.7		0.8	ns
t_{CASC}		0.7		0.9		1.0	ns
t_{C}		0.9		1.0		1.2	ns
t_{CO}		0.2		0.3		0.3	ns
t_{COMB}		0.6		0.7		0.8	ns
t_{SU}	0.8		1.0		1.2		ns
t_{H}	0.3		0.5		0.5		ns
t_{PRE}		0.3		0.3		0.4	ns
t_{CLR}		0.3		0.3		0.4	ns
t_{CH}	2.5		3.5		4.0		ns
t_{CL}	2.5		3.5		4.0		ns

Table 100. EPF10K100A Device IOE Timing Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{IOD}		2.5		2.9		3.4	ns
t_{IOC}		0.3		0.3		0.4	ns
t_{IOCO}		0.2		0.2		0.3	ns
t_{IOCOMB}		0.5		0.6		0.7	ns
t_{IOSU}	1.3		1.7		1.8		ns
t_{IOH}	0.2		0.2		0.3		ns
t_{IOCLR}		1.0		1.2		1.4	ns
t_{OD1}		2.2		2.6		3.0	ns
t_{OD2}		4.5		5.3		6.1	ns
t_{OD3}		6.8		7.9		9.3	ns
t_{XZ}		2.7		3.1		3.7	ns
t_{ZX1}		2.7		3.1		3.7	ns
t_{ZX2}		5.0		5.8		6.8	ns
t_{ZX3}		7.3		8.4		10.0	ns
t_{INREG}		5.3		6.1		7.2	ns
t_{IOFD}		4.7		5.5		6.4	ns
t_{INCOMB}		4.7		5.5		6.4	ns

Table 113. ClockLock & ClockBoost Parameters (Part 2 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
$f_{CLKDEV1}$	Input deviation from user specification in MAX+PLUS II (ClockBoost clock multiplication factor equals 1) *(1)*			±1	MHz
$f_{CLKDEV2}$	Input deviation from user specification in MAX+PLUS II (ClockBoost clock multiplication factor equals 2) *(1)*			±0.5	MHz
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)			100	ps
t_{LOCK}	Time required for ClockLock or ClockBoost to acquire lock *(2)*			10	µs
t_{JITTER}	Jitter on ClockLock or ClockBoost-generated clock *(3)*			1	ns
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock	40	50	60	%

Notes:

(1) To implement the ClockLock and ClockBoost circuitry with the MAX+PLUS II software, designers must specify the input frequency. The MAX+PLUS II software tunes the PLL in the ClockLock and ClockBoost circuitry to this frequency. The f_{CLKDEV} parameter specifies how much the incoming clock can differ from the specified frequency during device operation. Simulation does not reflect this parameter.

(2) During device configuration, the ClockLock and ClockBoost circuitry is configured before the rest of the device. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration, because the t_{LOCK} value is less than the time required for configuration.

(3) The t_{JITTER} specification is measured under long-term observation.

Power Consumption

The supply power (P) for FLEX 10K devices can be calculated with the following equation:

$$P = P_{INT} + P_{IO} = (I_{CCSTANDBY} + I_{CCACTIVE}) \times V_{CC} + P_{IO}$$

Typical $I_{CCSTANDBY}$ values are shown as I_{CC0} in the FLEX 10K device DC operating conditions tables on pages 46, 49, and 52 of this data sheet. The $I_{CCACTIVE}$ value depends on the switching frequency and the application logic. This value is calculated based on the amount of current that each LE typically consumes. The P_{IO} value, which depends on the device output load characteristics and switching frequency, can be calculated using the guidelines given in *Application Note 74 (Evaluating Power for Altera Devices)*.

Compared to the rest of the device, the embedded array consumes a negligible amount of power. Therefore, the embedded array can be ignored when calculating supply current.

The $I_{CCACTIVE}$ value is calculated with the following equation:

$$I_{CCACTIVE} = K \times \mathbf{f_{MAX}} \times N \times \mathbf{tog_{LC}} \times \frac{\mu A}{MHz \times LE}$$

The parameters in this equation are shown below:

Notes: